

STPS40M100C

Power Schottky rectifier

Features

- High current capability
- Avalanche rated
- Low forward voltage drop current
- High frequency operation

Description

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB and I²PAK, this device is intended to be used in notebook, game station and desktop adaptors, providing in these applications a good efficiency at both low and high load.

Table 1. Device summary

Symbol	Value		
I _{F(AV)}	2 x 20 A		
V _{RRM}	100 V		
T _j (max)	150 °C		
V _F (typ)	0.420 V		

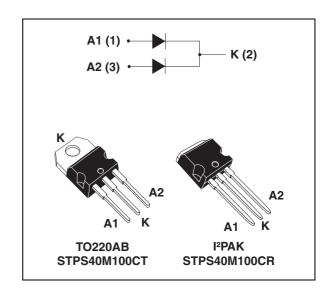
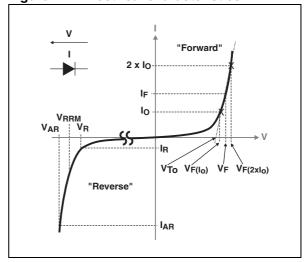


Figure 1. Electrical characteristics (a)



a. V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 11* V_{AR} and I_{AR} are pulse measurements ($t_p < 1~\mu s$). V_R , I_R , V_{RRM} and V_F , are static characteristics

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1 Characteristics

Table 2. Absolute ratings (limiting values per diode at 25 °C unless otherwise stated)

Symbol	Parameter				Unit
V_{RRM}	Repetitive peak reverse voltage			100	V
I _{F(RMS)}	Forward current rms			60	Α
1	Average forward current $\delta = 0.5$	T _c = 125 °C	Per diode	20	Α
^I F(AV)	Average lorward current 6 = 0.5	T _c = 120 °C	Per package	40	
I _{FSM}	Surge non repetitive forward current	urrent t _p = 10 ms sinusoidal			Α
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power $t_p = 1 \mu s T_j = 25 ^{\circ}C$			23 200	W
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage $t_p < 1 \mu s$ $T_j < 150 ^{\circ}C$, $t_{AR} < 58 A$		120	V	
V _{ASM} ⁽²⁾	Maximum single pulse peak avalanche voltage $ t_p < 1 \; \mu s \; T_j < 150 \; ^{\circ}C, \; I_{AR} < 58 \; A$			120	V
T _{stg}	Storage temperature range			-65 to + 175	°C
T _j	Maximum operating junction temperature (3)			150	°C

For temperature or pulse time duration deratings, refer to Figure 4. and Figure 5.. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

Table 3. Thermal resistance

Symbol		Parameter	Value	Unit	
R _{th(j-c)} Junction to case	lunction to case	Per diode	1.4	°C/W	
	Total	0.95	C/VV		
R _{th(c)}	Coupling		0.5	°C/W	

When diodes 1 and 2 are used simultaneously

 $T_j(diode\ 1) = P(diode\ 1) \times R_{th(j-c)}(Per\ diode) + P(diode\ 2) \times R_{th(c)}$

Table 4. Static electrical characteristics

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾ Reverse leakage current		T _j = 25 °C	$V_R = V_{RRM}$	-	-	70	μΑ
	Poverce leakage ourrent	T _j = 125 °C		-	15	70	mA
	neverse leakage current	T _j = 25 °C	V _R = 70 V	-	-	40	μΑ
		T _j = 125 °C		-	7.5	40	mA
		T _j = 125 °C	I _F = 5 A	-	0.415	0.500	V
V _F ⁽²⁾	Forward voltage drop	T _j = 125 °C	I _F = 10A	-	0.500	0.560	-
		T _j = 25 °C	I _F = 20 A	-	-	0.780	-
		T _j = 125 °C		-	0.585	0.640	-

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.560 \times I_{F(AV)} + 0.004 \times I_{F}^{2}_{(RMS)}$$

^{2.} Refer to Figure 11

^{3.} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

^{2.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

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Figure 2. Average forward power dissipation Figure 3. Average forward current per diode versus average forward current versus ambient temperature (per diode) $(\delta = 0.5)$

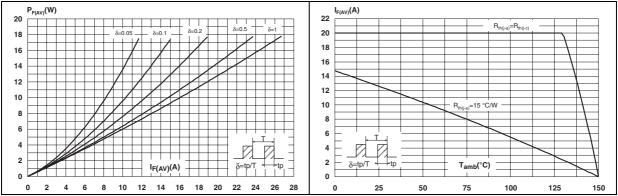


Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Normalized avalanche power derating versus junction temperature

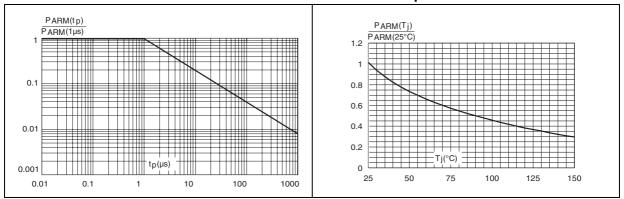
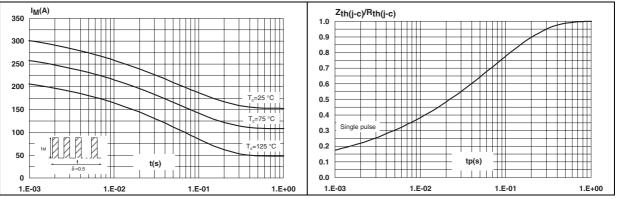


Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values per diode)

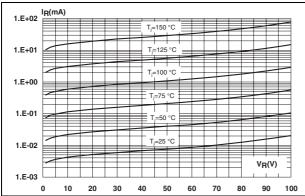
Figure 7. Relative variation of thermal impedance junction to case versus pulse duration



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Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)



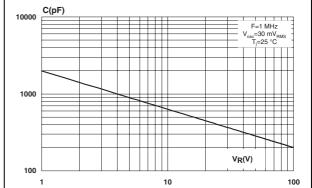
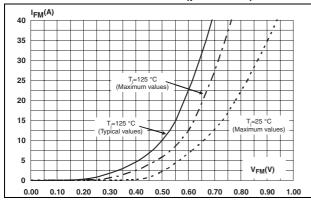
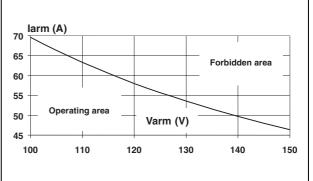


Figure 10. Forward voltage drop versus forward current (per diode)

Figure 11. Reverse safe operating area $(t_p < 1 \mu s \text{ and } T_i < 150 \,^{\circ}\text{C})$





2 Package information

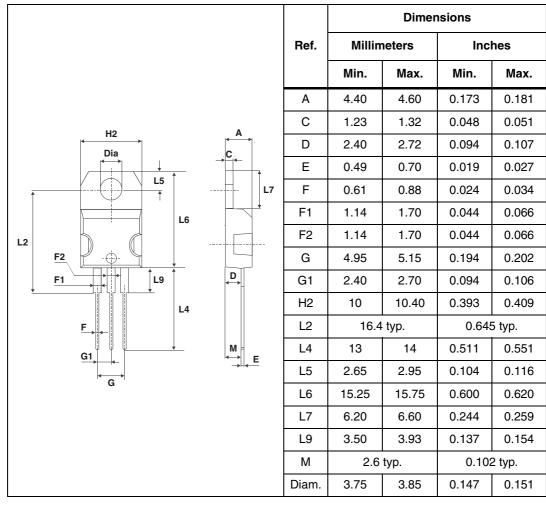
Epoxy meets UL94, V0

Cooling method: conduction

Recommended torque value: 0.4 to 0.6 N⋅m

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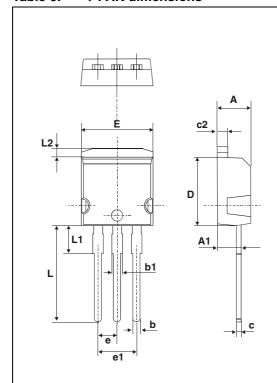
Table 5. TO-220AB dimensions



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Mounting (soldering) the I2PAK metal slug (heatsink) with alloy, like a surface mount device, IS NOT PERMITTED. A standard through-hole mounting is mandatory.

Table 6. I²PAK dimensions



	Dimensions				
Ref.	Millimeters		Inches		
	Min. Max.		Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.40	2.72	0.094	0.107	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.044	0.067	
С	0.49	0.70	0.019	0.028	
c2	1.23	1.32	0.048	0.052	
D	8.95	9.35	0.352	0.368	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
Е	10	10.40	0.394	0.409	
L	13	14	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L2	1.27	1.40	0.050	0.055	

3 Ordering information

 Table 7.
 Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS40M100CT	STPS40M100CT	TO-220AB	1.9 g	50	Tube
STPS40M100CR	STPS40M100CR	I ² PAK	1.5 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
25-Mar-2009	1	First issue.
10-Apr-2010	2	Updated package graphics.
29-Apr-2010	3	Added I ² PAK package. Updated weight in <i>Table 7</i> .

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